

Supplementary Informations for

High-Performance Carbon Nanotube Network Transistors Fabricated Using a Hole Punching Technique

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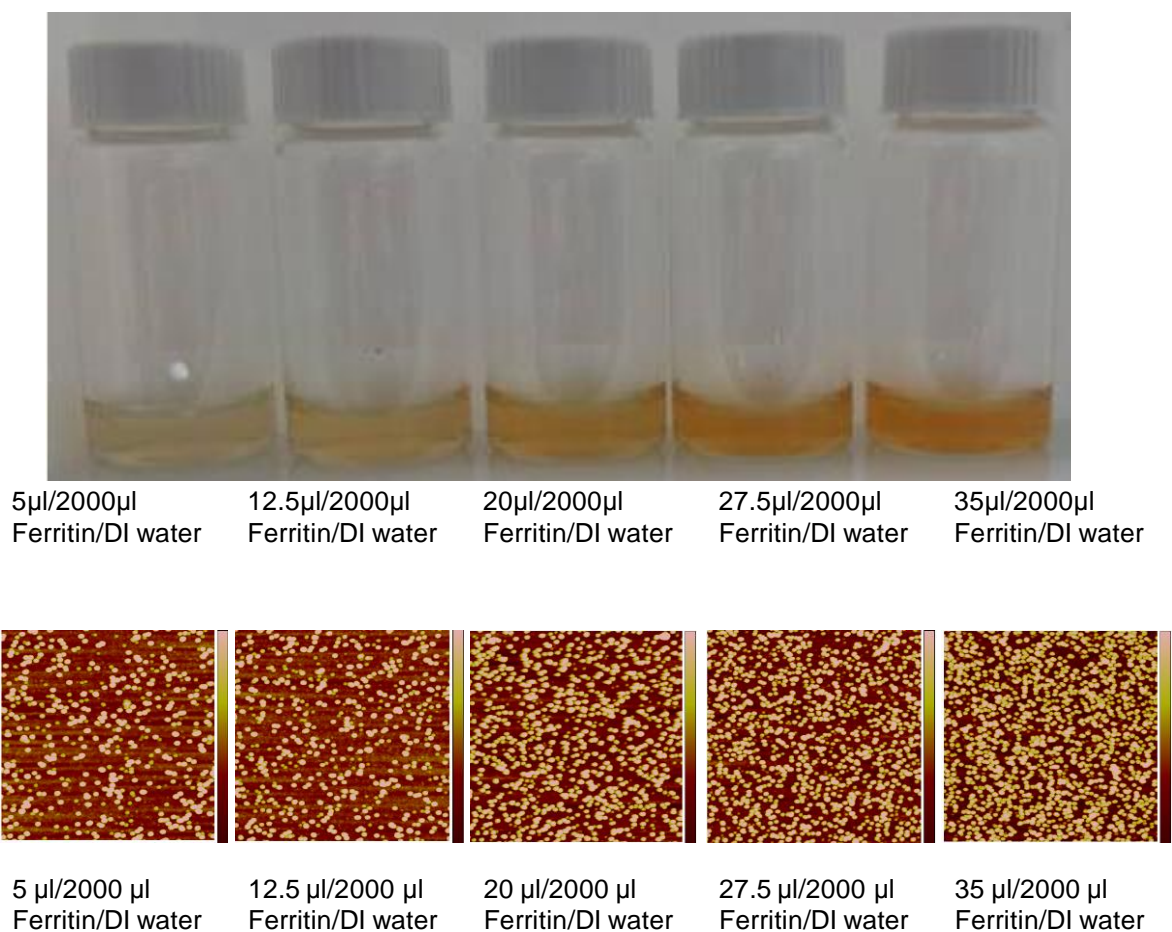


Fig. S1. AFM images of ferritin catalysts from various concentrations of ferritin.

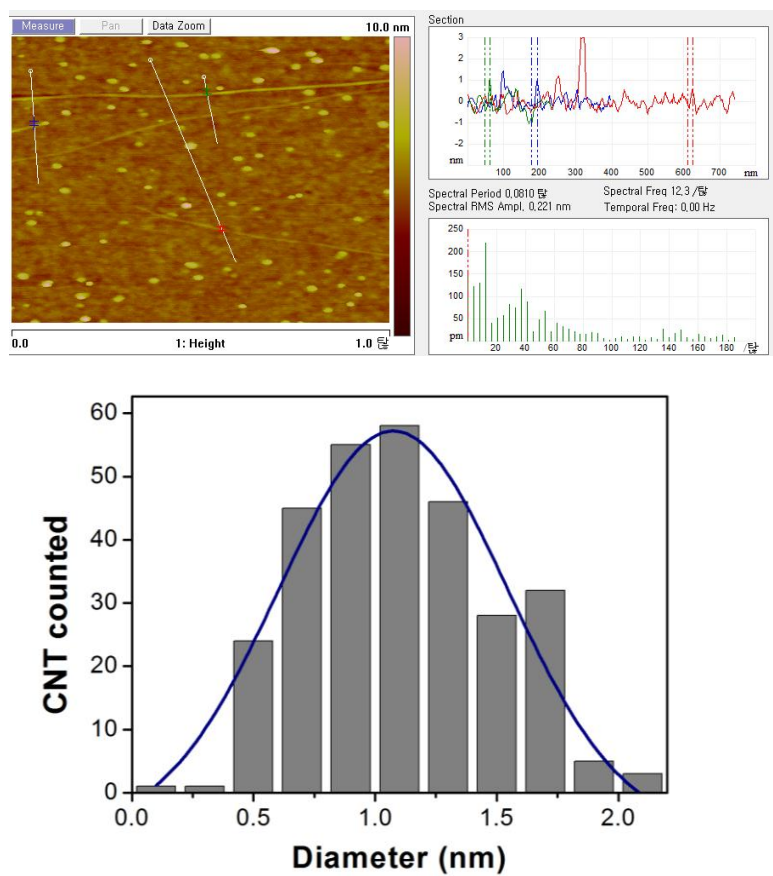


Fig. S2. Diameter distribution in SWNTs grown from ferritin as catalysts

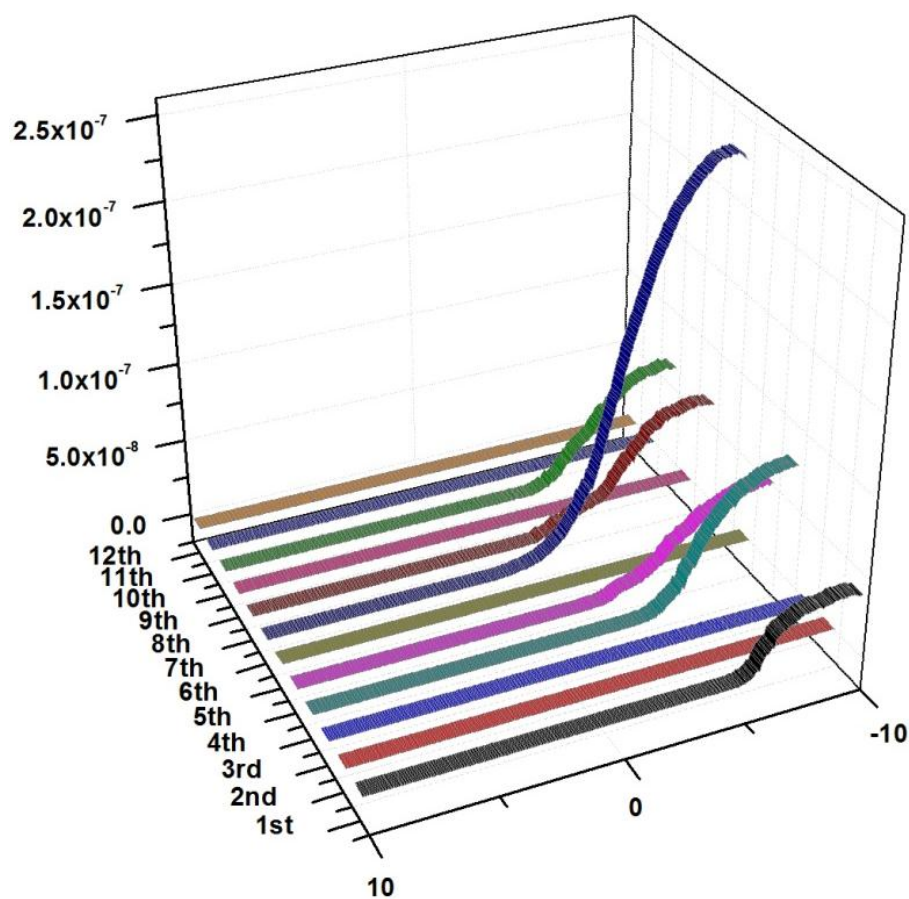


Fig. S3. Transfer curves measured from 12 low-density (below percolation threshold) SWNT-FETs. As shown in the figure, 6 devices out of 12 do not show measurable conductance.

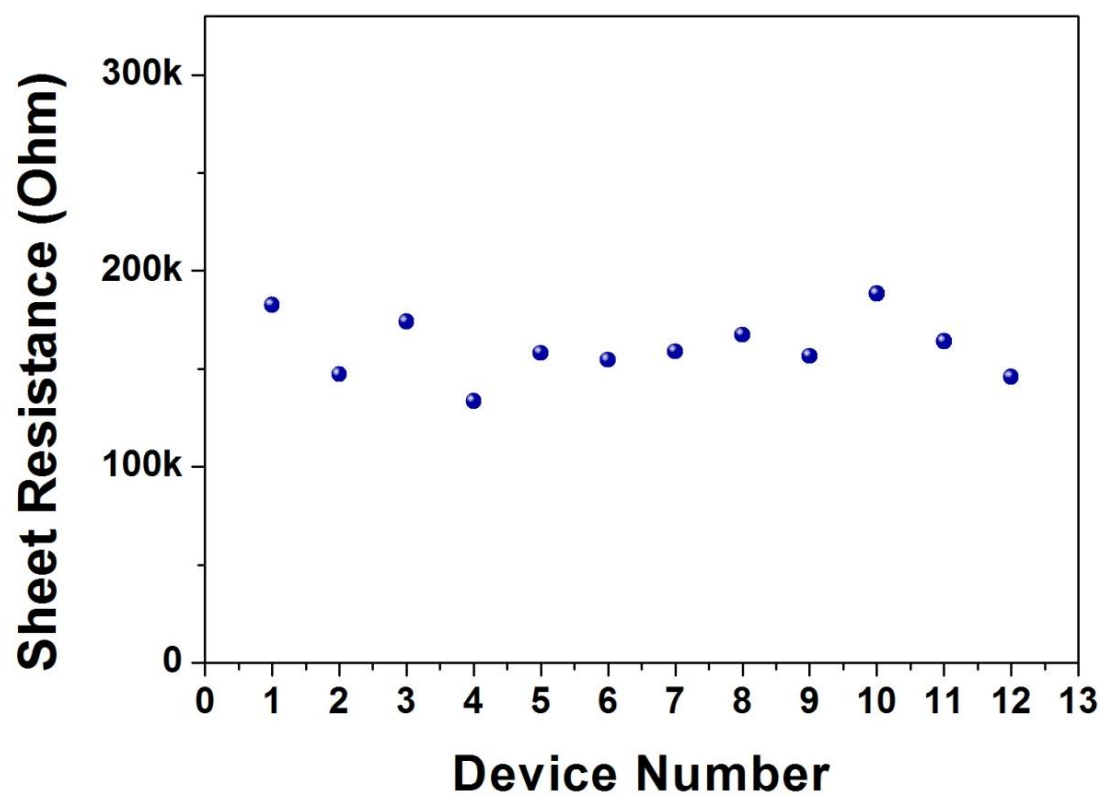


Fig. S4. Sheet resistance from SWNT networks with densities $\sim 0.99/\mu\text{m}^2$ and lengths of $1.42\mu\text{m}$.